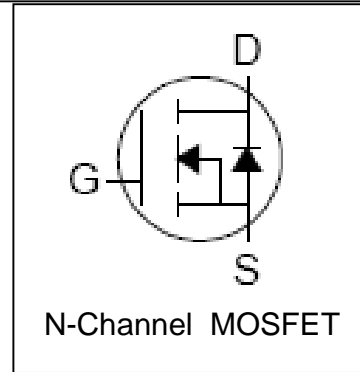
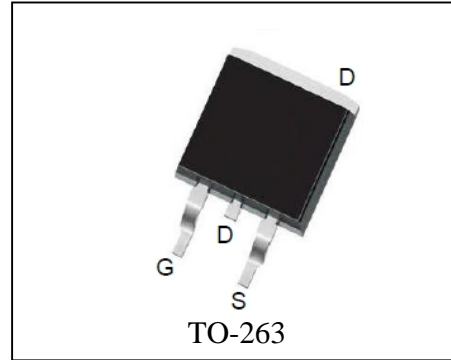


### Features

- 100V/40A,  
 $R_{DS(ON)} = 21m$  (Typ.) @  $V_{GS} = 10V$
- Super High Dense Cell Design
- 100% avalanche tested
- Lead Free and Green Devices Available  
 (RoHS Compliant)

### Pin Description



### Applications

- Switching application

### Absolute Maximum Ratings

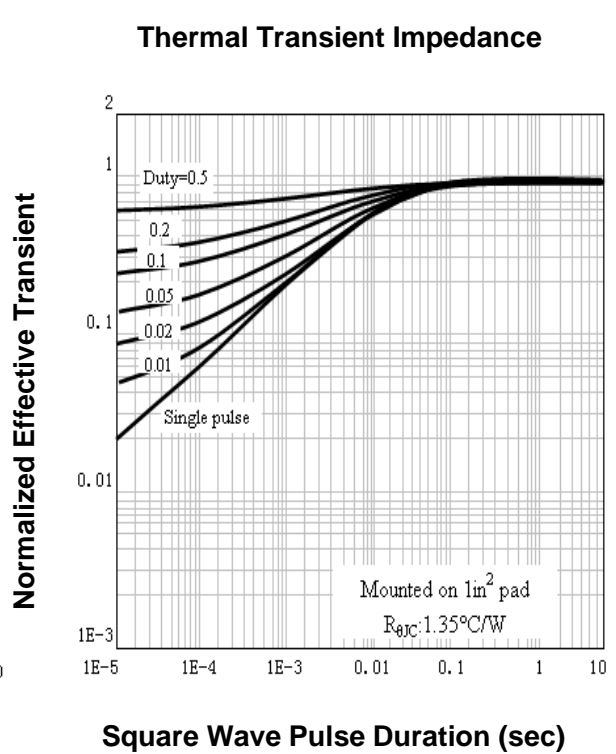
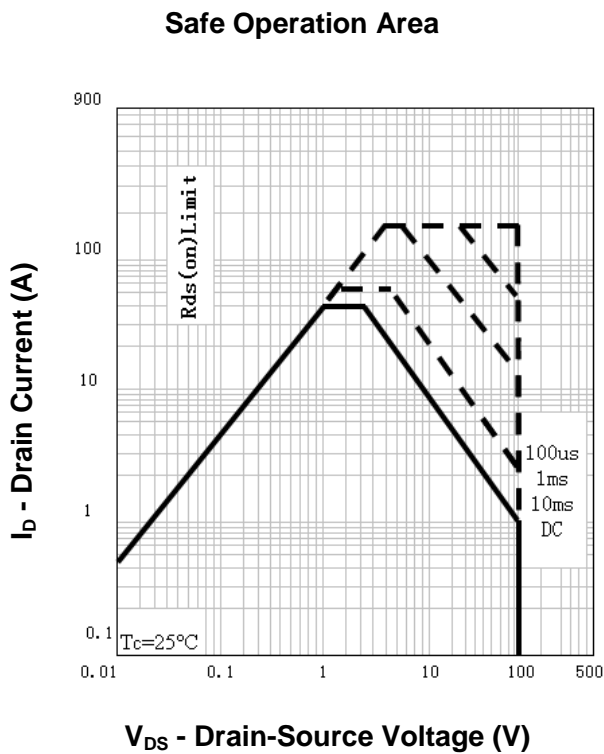
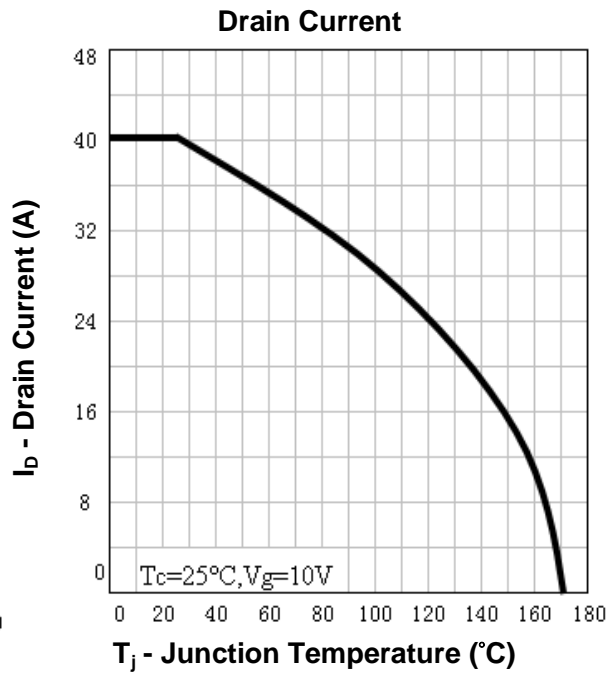
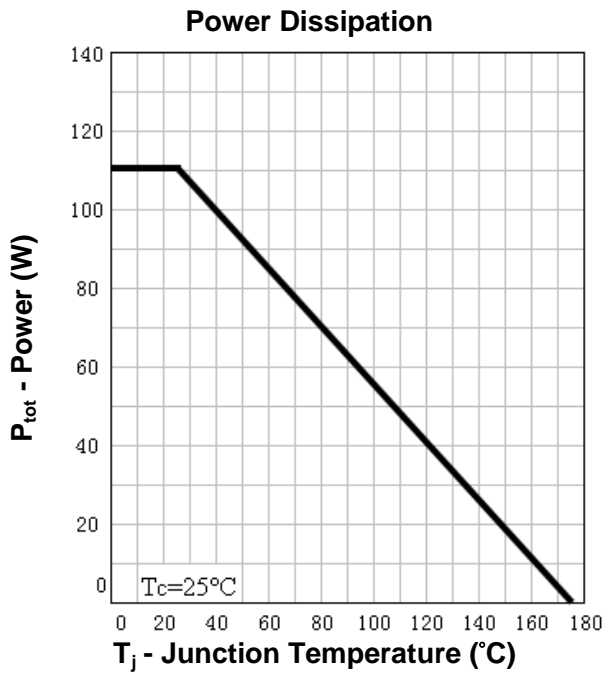
Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_A = 25^\circ C$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	100	V
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	
$T_J$	Maximum Junction Temperature	175	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$I_S$	Diode Continuous Forward Current	$T_C = 25^\circ C$ 40	A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}$	300 $\mu s$ Pulse Drain Current Tested	$T_C = 25^\circ C$ 160 <sup>①</sup>	A
$I_D$	Continuous Drain Current ( $V_{GS} = 10V$ )	$T_C = 25^\circ C$ 40 <sup>②</sup>	A
		$T_C = 100^\circ C$ 27	
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$ 111	W
		$T_C = 100^\circ C$ 56	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.35	$^\circ C/W$
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}$ <sup>③</sup>	Avalanche Energy, Single Pulsed	220	mJ

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1H35S			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1 10	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			$\pm 100$	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=16A$		21	25	m $\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=16A, V_{GS}=0V$		0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=16A, di_{SD}/dt=100A/\mu s$		100		ns
$Q_{rr}$	Reverse Recovery Charge			430		nC
<b>Dynamic Characteristics</b> <sup>(5)</sup>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		2.8		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Frequency=1.0MHz		2100		pF
$C_{oss}$	Output Capacitance			250		
$C_{riss}$	Reverse Transfer Capacitance			115		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=50V, R_L=30\Omega,$ $I_{DS}=16A, V_{GEN}=10V,$ $R_G=4.7\Omega$		22		ns
$t_r$	Turn-on Rise Time			76		
$t_{d(OFF)}$	Turn-off Delay Time			60		
$t_f$	Turn-off Fall Time			23		
<b>Gate Charge Characteristics</b> <sup>(5)</sup>						
$Q_g$	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V,$ $I_{DS}=16A$		44		nC
$Q_{gs}$	Gate-Source Charge			10		
$Q_{gd}$	Gate-Drain Charge			21		

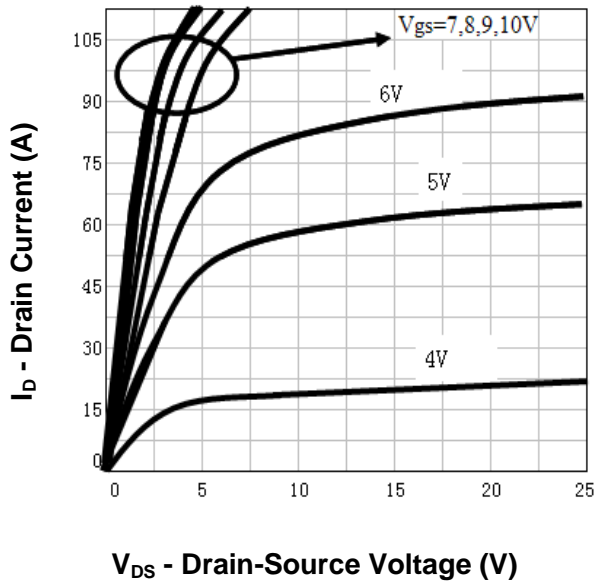
- Notes: ① Pulse width limited by safe operating area.  
 ② Calculated continuous current based on maximum allowable junction temperature.  
 ③ Limited by  $T_{Jmax}, I_{AS}=21A, V_{DD}=48V, R_G=50\Omega$ , Starting  $T_J=25^\circ\text{C}$ .  
 ④ Pulse test; Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .  
 ⑤ Guaranteed by design, not subject to production testing.

**Typical Characteristics**

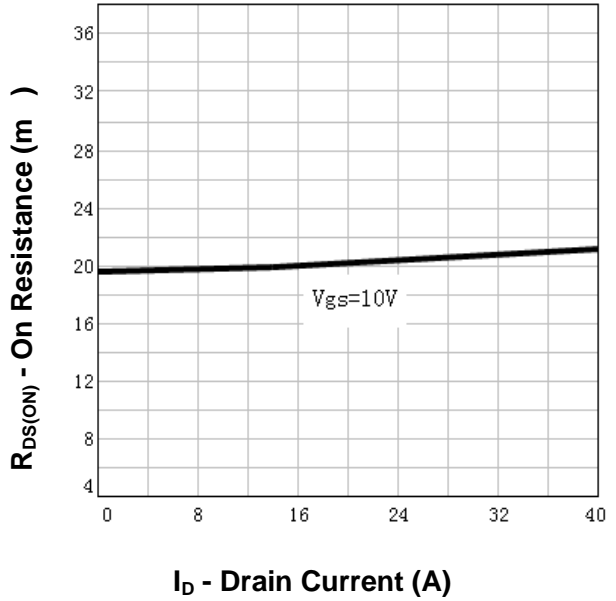


**Typical Characteristics**

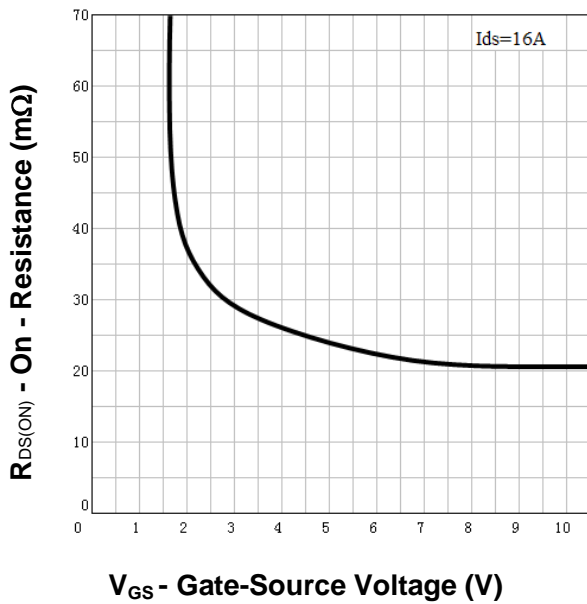
**Output Characteristics**



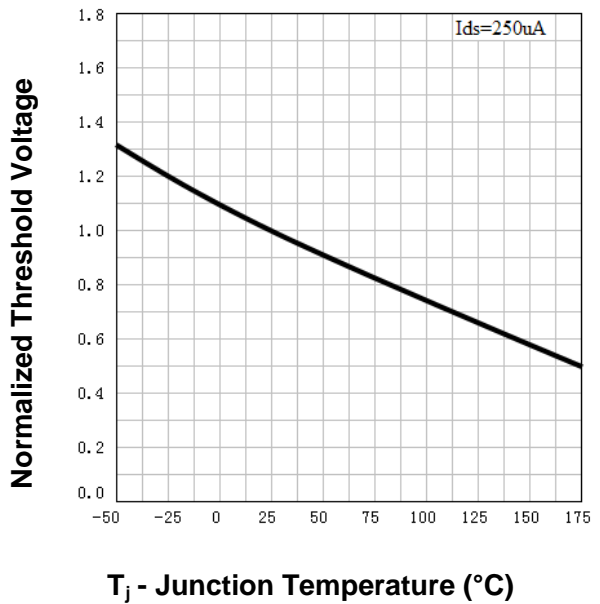
**Drain-Source On Resistance**



**Drain-Source On Resistance**

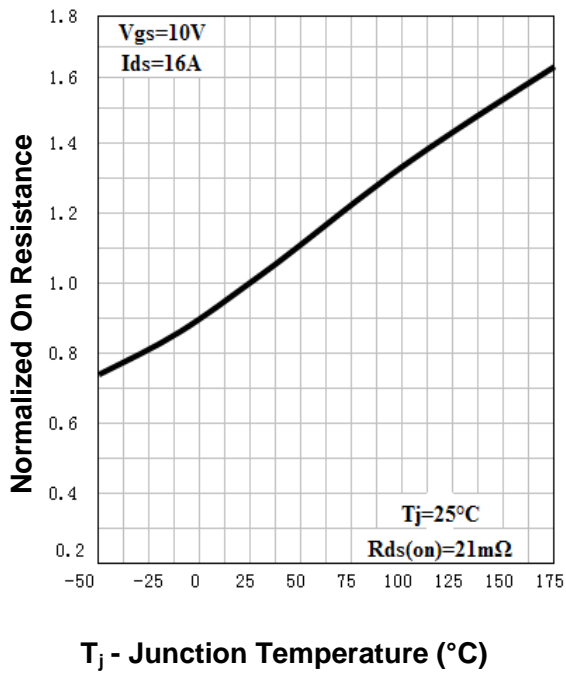


**Gate Threshold Voltage**

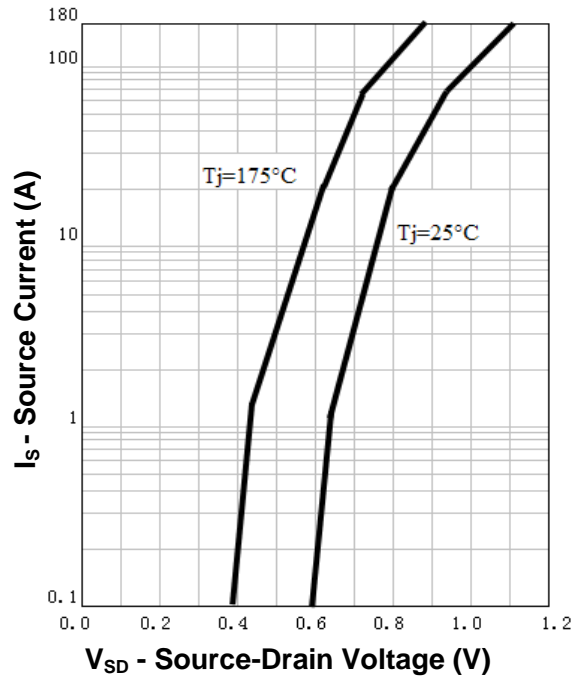


**Typical Characteristics**

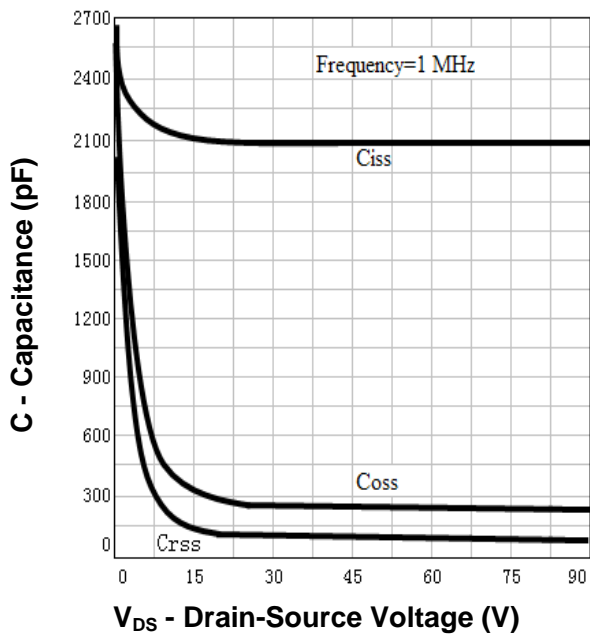
**Drain-Source On Resistance**



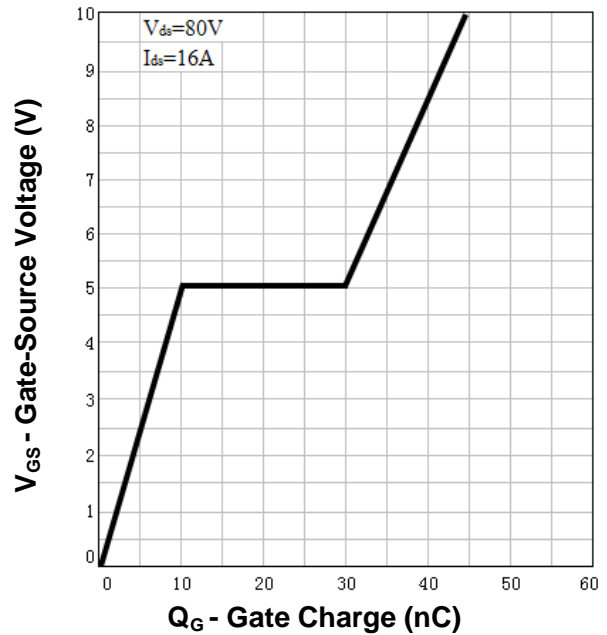
**Source-Drain Diode Forward**



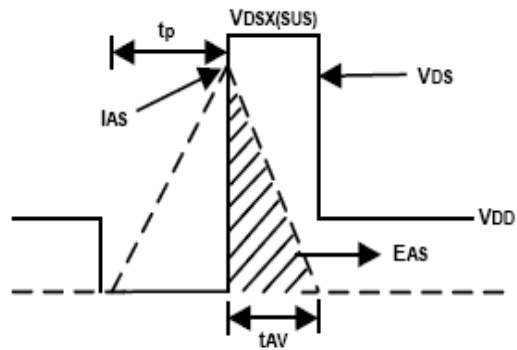
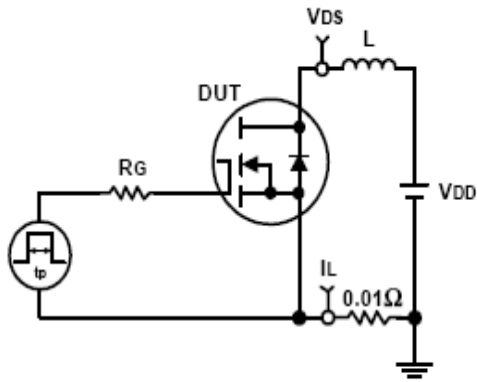
**Capacitance**



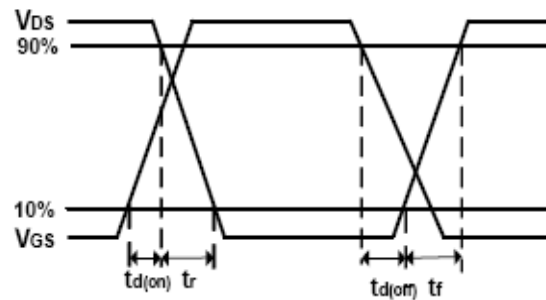
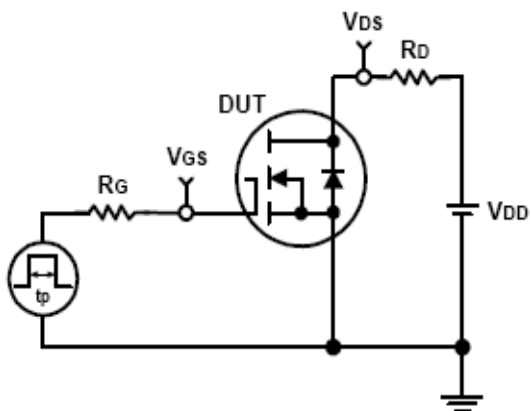
**Gate Charge**



**Avalanche Test Circuit and Waveforms**



**Switching Time Test Circuit and Waveforms**

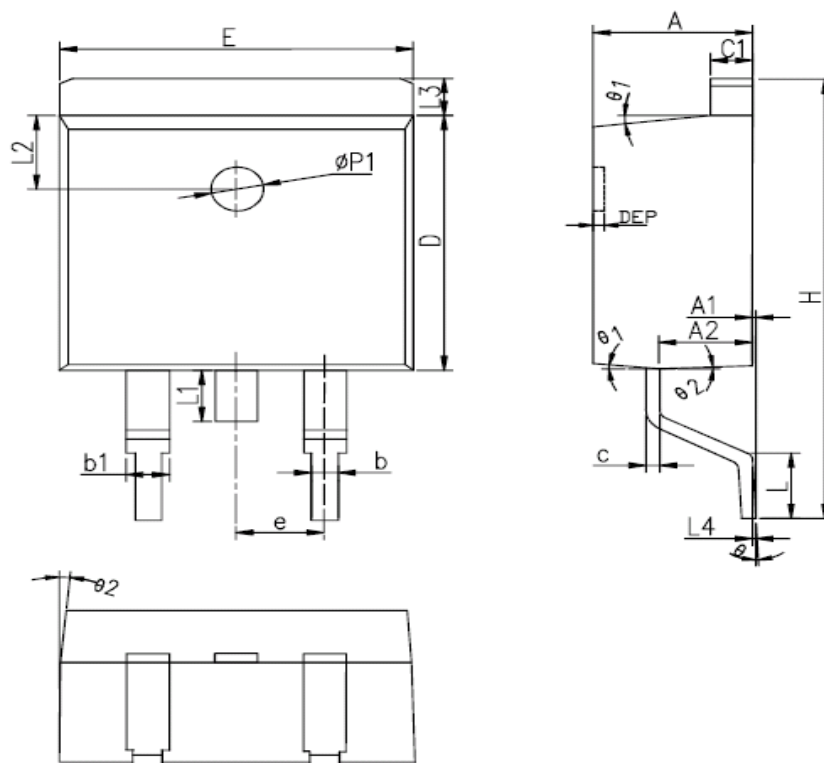


**Ordering and Marking Information**

<b>Device</b>	<b>Marking</b>	<b>Package</b>	<b>Packaging</b>	<b>Quantity</b>	<b>Reel Size</b>	<b>Tape width</b>
RU1H35S	RU1H35S	TO-263	Tube	50	-	-

**Package Information**

**TO-263-2L**



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			Øp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

ALL DIMENSIONS REFER TO JEDEC STANDARD  
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS



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